

## Amendments to the CLAIMS

Please amend claims 1-4 as follows:

1. (Currently Amended) A method for forming a floating gate in a flash memory device, comprising the steps of:

- (a) providing a semiconductor substrate on which a tunnel oxide film and a first polysilicon film are formed;
- (b) sequentially forming a buffer oxide film and a pad nitride film on the first polysilicon film sequentially;
- (c) forming a trench in the semiconductor substrate;
- (d) depositing a device isolation oxide film to ~~bury~~ fill the trench, and then performing a planarization process using the pad nitride film as a barrier;
- (e) carrying out a strip process to simultaneously remove the pad nitride film and at least 50% of the buffer oxide film, leaving a reduced buffer oxide film on the first polysilicon film at the same time;
- (f) removing the reduced buffer oxide film using a pre-treatment cleaning process; and
- (g) depositing a second polysilicon film on a whole the resulting structure and patterning the second polysilicon film through with a patterning process, ~~whereby forming a~~ to form the floating gate including the first polysilicon film and the second polysilicon film.

2. Currently Amended) The method of claim 1, wherein the buffer oxide film is deposited in part (b) with a thickness in the range of 30 Å to 40Å.

3. (Currently Amended) The method of claim 1, wherein the buffer oxide film is deposited using high temperature oxide (HTO), a tetra ethyl ortho silicate (TEOS), and a DCS-HTO (DiChloroSilane ( $\text{SiH}_2\text{Cl}_2$ )-HTO).

4. (Currently Amended) The method of claim 1, after the step part (c) and before part (d), further comprising a step of performing a wall oxidation process for forming a wall oxide film on an inner surface of the trench and on inside walls of the tunnel oxide film, the first polysilicon film, and the buffer oxide film.

5. (Original) The method of claim 4, wherein the wall oxidation process is carried out at a temperature in the range of 800°C to 1000°C.